
24V, 2.5 μ A I_q, High PSRR, 300mA Low-Dropout LDO

Description

The HM73XXH series are high accuracy, CMOS LDO Voltage Regulators, offering Low Power Consumption, high ripple rejection ratio and low dropout. Internally, The HM73XXH includes a reference voltage source, error amplifiers, driver transistors, current limiters and phase compensators. The HM75XXM's current limiters' foldback circuit also operates as a short protect for the output current limiter and the output pin.

The HM73XXH series is also fully compatible with low ESR ceramic capacitors, reducing cost and improving output stability. This high level of output stability is maintained even during frequent load fluctuations, due to the excellent transient response performance and high PSRR achieved across a broad range of frequencies. The CE function allows the output of regulator to be turned off, resulting in greatly reduced power consumption, ideal for powering the battery equipment to a longer service life.

Features

- Low Power Consumption: 2.5 μ A (Typ)
- Maximum Output Current: 300mA
- Low Dropout Voltage: 180mV@100mA (V_{OUT}=3.3V)
- Operating Voltage Range: 2.5V ~ 24V
- Output Voltage Accurate: $\pm 1\%$
- High PSRR: 65dB @1kHz
- Good Transient Response
- Integrated Short-Circuit Protection
- Over-Temperature Protection
- Output Current Limit
- Fast discharge function.
- Low Temperature Coefficient
- Stable with Ceramic Capacitor
- RoHS Compliant and Lead (Pb) Free
- -40 $^{\circ}$ C to +85 $^{\circ}$ C Operating Temperature Range
- Fixed Output Voltage Versions: 1.2, 1.5, 1.8, 2.5, 2.8, 3.0, 3.3, 3.6, 4.0, 4.2, 4.4 and 5.0V
- Available in Green SOT23-3, SOT23-5, SC70-5, DFN1x1-4L, SOT89-3 Packages

Applications

- Portable, Battery Powered Equipment
 - Smoke detector and sensor
 - Audio/Video Equipmen
 - Weighting Scales
 - Home Automation
 - Electronic fingerprint lock
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Application Circuits

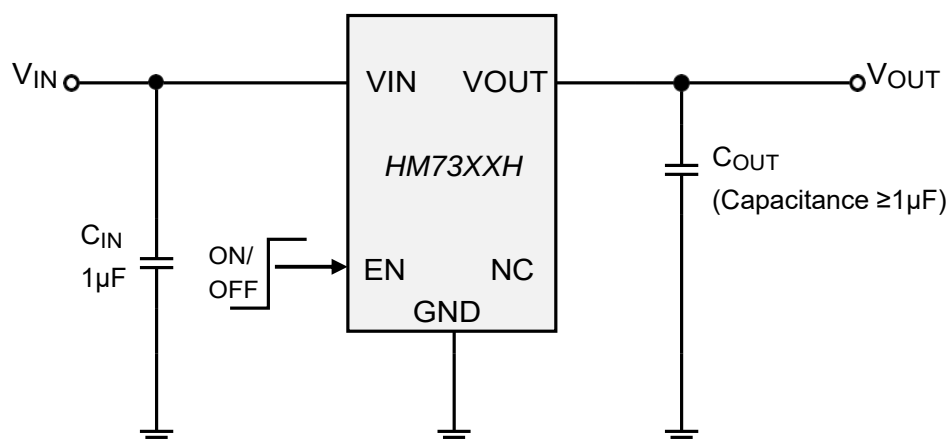
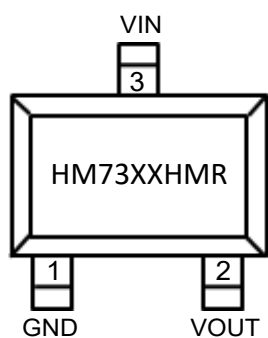
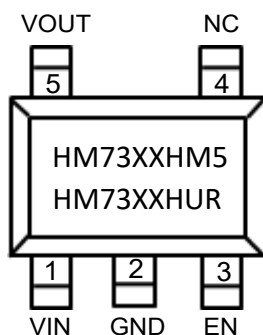


Figure 1. HM73XXH Typical Application Circuit

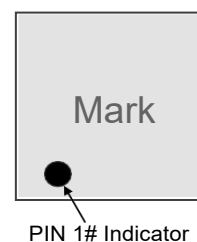
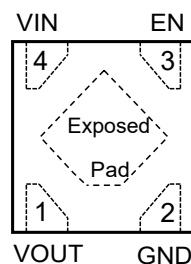
Pin Configuration (TOP VIEW)



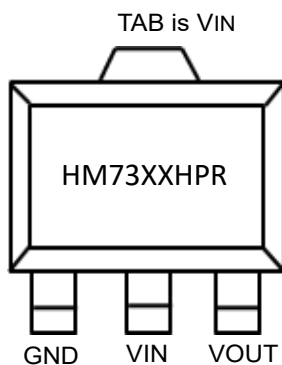
SOT23-3



SOT23-5 / SC70-5



HM73XXHDR
DFN-4L (1mm × 1mm)
0.4mm height(max), 0.65mm pitch



Pin Description

Pin No.					Pin Name	Pin Function
SOT23-3	SC70-5	SOT23-5	DFN1X1-4	SOT89-3		
1	2	2	2	1	GND	Ground
3	1	1	4	2	VIN	Power Input
2	5	5	1	3	VOUT	Output Voltage
-----	3	3	3	-----	EN	Enable Control Input
-----	4	4	-----	-----	NC	No Connect
EP / TAB	In PCB layout, prefer to use large copper area to cover this pad for better thermal dissipation					

Order Information

HM73XXH①②

Designator	Symbol	Description
①②	MR/M5/tR/5R/1W	SOT23-3L , SOT23-5L , SC70-5L , DFN1x1-4L ,SOT89-3L
XX	Integer e.g 1.8=18	Output Voltage :1.2,1.5,1.8,2.5,2.8,3.0,3.3,3.6,4.0,4.2,4.4 and 5.0V

Part NO.	Description	Package	T/R Qty
HM73XXHMR	HM73XXH 24V ,2.5μA Iq ,High PSRR ,300mA Low-Dropout LDO	SOT23-3L	3,000 PCS
HM73XXHM5		SOT23-5L	3,000 PCS
HM73XXHUR		SC70-5L	3,000 PCS
HM73XXHDR		DFN1x1-4L	1,0000 PCS
HM73XXHPR		SOT89-3L	1,000 PCS

Marking Information

For marking information, contact our sales representative directly

Absolute Maximum Ratings

Item		Symbol	Rating	Unit
Supply Input Voltage		V _{IN}	-0.3 ~ 30	V
EN to GND		V _{EN}	-0.3 ~ 30	V
Regulated Output Voltage		V _{OUT}	-0.3 ~ 6.0	V
Output Current		I _{OUT}	Internally limited	mA
Power Dissipation P _D @T _A =+25°C	SOT23-3L	P _D	450	mW
	SOT23-5L		500	
	SC70-5L		400	
	DFN1x1-4L		450	
	SOT89-3L		700	
Thermal Resistance (Junction to air)	SOT23-3L	θ _{JA}	275	°C /W
	SOT23-5L		250	
	SC70-5L		315	
	DFN1x1-4L		275	
	SOT89-3L		180	
Human Body Model (HBM)		±4000		V
Charged Device Mode (CDM)		±2000		V
Machine Mode (MM)		200		V
Storage Temperature Range		T _{STG}	-65 ~ +150	°C
Operating Junction Temperature		T _J	+150	°C
Lead Temperature (Soldering 10s)		T _{LEAD}	+260	°C

Note:

- 1、Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these conditions is not implied. Exposure to absolute-maximum-rated conditions for extended period may affect device reliability.
- 2、Ratings apply to ambient temperature at +25°C
- 3、The package thermal impedance is calculated in accordance to JESD 51-7.

Recommended Operating Conditions

Item	Min	Max	Unit
Operating Ambient Temperature	-40	+85	°C
Input Voltage	2.5	12	V
Output Voltage	1.8	5.0	V

Electronic Characteristics

Test Conditions: $V_{IN} = V_{OUT} + 1V$, $C_{IN}=C_{OUT}=1\mu F$, $T_A=25^{\circ}C$, unless otherwise specified

Parameter	Symbol	Test Conditions		Min	Typ	Max	Unit
Input Voltage	V _{IN}			2.5	—	24	V
Quiescent Current	I _Q	V _{IN} =12V, I _{LOAD} =0mA		—	2.5	—	μA
Shutdown Current	I _{SHDN}	EN=0 V, V _{OUT} =0 V			0	0.01	μA
Output Voltage	V _{OUT}	V _{IN} =12V, I _{LOAD} =1mA		V _{OUT} x 0.99	—	V _{OUT} x 1.01	V
Output Current	I _{OUT}	V _{IN} = V _{OUT} +1V		300	—	—	mA
Dropout Voltage V _{OUT} =3.3V	V _{DROP}	I _{LOAD} =100mA		—	180	—	mV
Line Regulation	Δ V _{LINE}	I _{LOAD} =10mA V _{OUT} +1.0V ≤ V _{IN} ≤ 20V		—	0.05	—	% / V
Load Regulation	Δ V _{LOAD}	V _{IN} = V _{OUT} +1V 1mA≤ I _{LOAD} ≤ 100mA		—	5	10	mV
EN Threshold Voltage	V _{CEH}	CE“High”Voltage		1.2	—	—	V
	V _{CEL}	CE“Low”Voltage		—	—	0.4	V
EN PIN Current	I _{EN}			—	0.1	—	μA
Current Limit	I _{LIMIT}			—	—	650	mA
Short Current	I _{SHORT}	V _{OUT} = GND		—	50	—	mA
Output Noise Voltage	V _{ON}	C _{OUT} =1μF, I _{LOAD} =10mA BW = 10Hz~100kHz		—	60	—	μVrms
Temperature Coefficient	Δ V _{OUT} / Δ T * V _{OUT}	I _{OUT} =1mA , T _A = - 40℃ ~ +85℃		—	± 50	—	ppm
Power Supply Rejection Rate	PSRR	V _{IN} = 4.3V	f=100Hz	—	75	—	dB
		V _{OUT} =3.3V	f=1KHz	—	65	—	dB
		I _{LOAD} =10mA	f=10KHz	—	50	—	dB
Thermal Shutdown Temperature	T _{SHDN}	—		—	160	—	℃
Thermal Shutdown Hysteresis	ΔT _{SHD}	—		—	20	—	℃

Note : All limits specified at room temperature ($T_A = 25^{\circ}C$) unless otherwise specified. All room temperature limits are 100% production tested. All limits at temperature extremes are ensured through correlation using standard Statistical Quality Control (SQC) methods. All limits are used to calculate Average Outgoing Quality Level (AOQL).

Functional Block Diagram

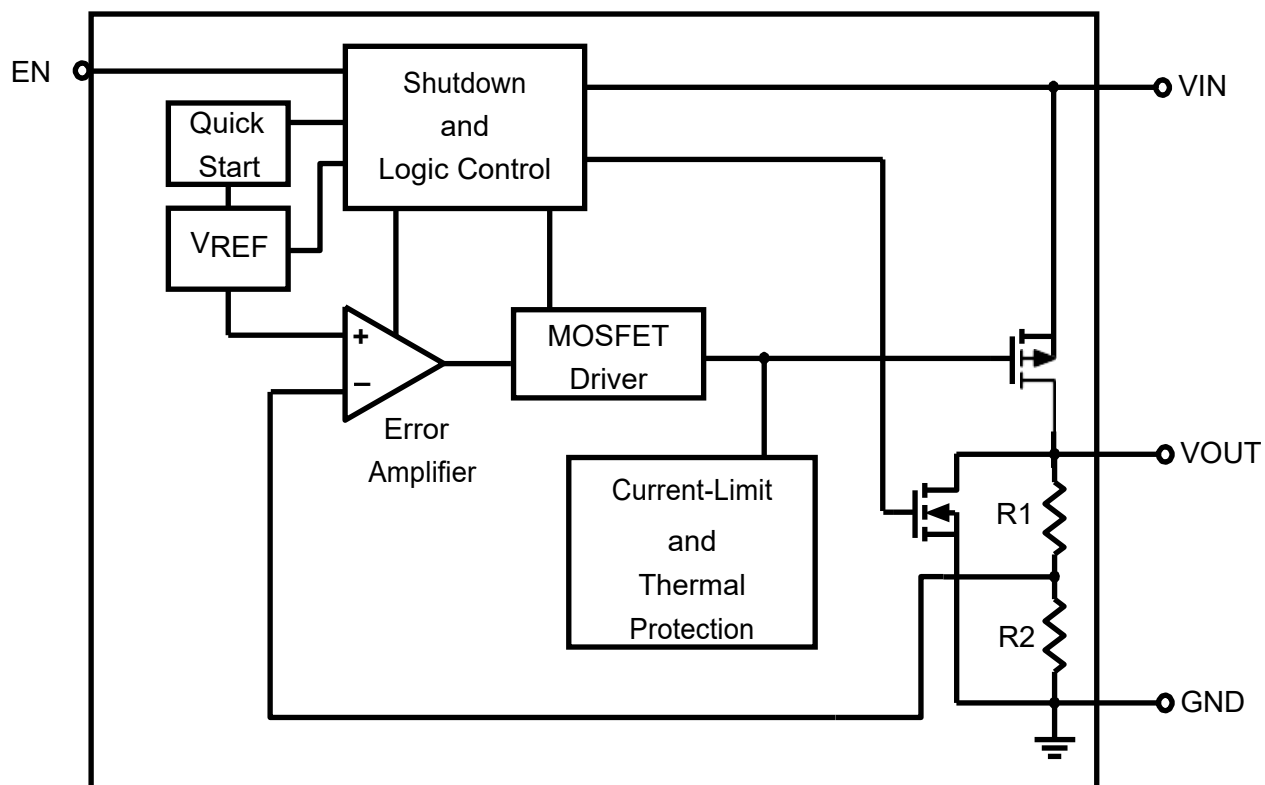
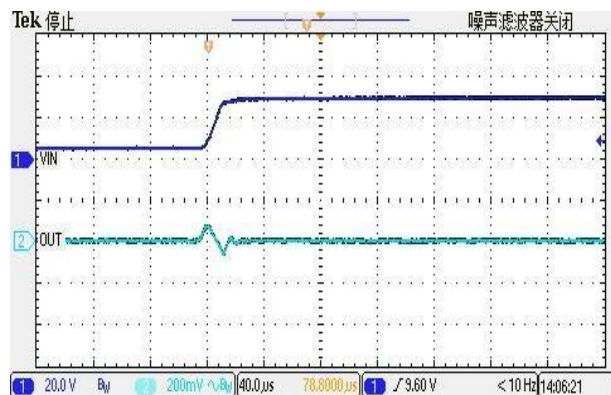
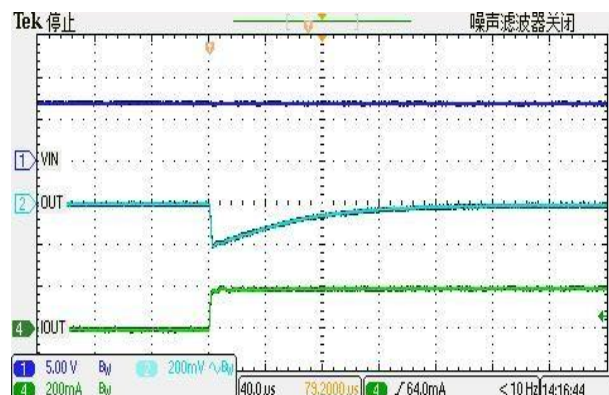


Figure 2. HM73XXH Block Diagram

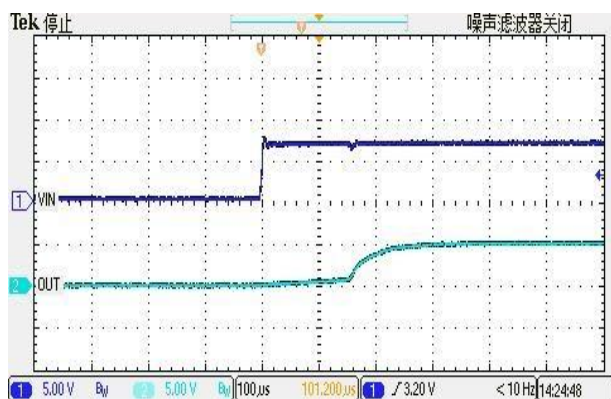
Typical Performance Characteristics



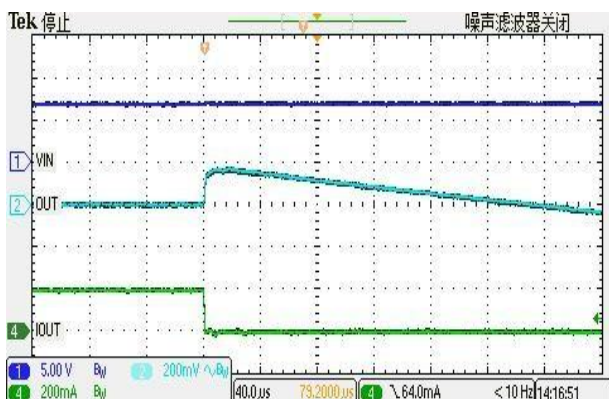
Line Transient Response
 $V_{IN}=5V-30V$, $V_{OUT}=5.0V$, $I_{OUT}=10mA$



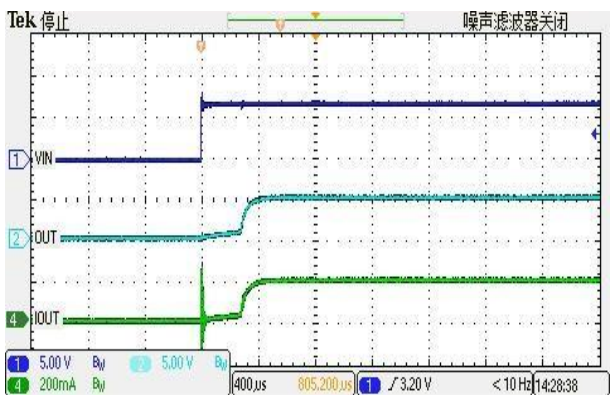
Load Transient Response
 $V_{IN}=7V$, $V_{OUT}=5V$, $I_{OUT}=1mA-200mA$



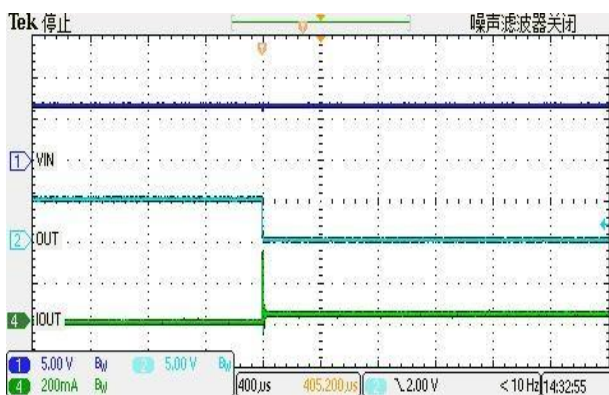
No Load Start
 $V_{IN}=7V$, $V_{OUT}=5V$, $I_{OUT}=0mA$



Load Transient Response
 $V_{IN}=7V$, $V_{OUT}=5V$, $I_{OUT}=200mA-1mA$



Load start
 $V_{IN}=7V$, $V_{OUT}=5V$, $I_{OUT}=200mA$



Power on short circuit
 $V_{IN}=7V$, $V_{OUT}=5V$

Application Guideline

■ Input Capacitor

A $\geq 1\mu\text{F}$ ceramic capacitor is recommended to connect between VIN and GND pins to decouple input power supply glitch and noise. The amount of the capacitance may be increased without limit. This input capacitor must be located as close as possible to the device to assure input stability and less noise. For PCB layout, a wide copper trace is required for both VIN and GND.

■ Output Capacitor

An output capacitor is required for the stability of the LDO. The recommended output capacitance is $\geq 1\mu\text{F}$, ceramic capacitor is recommended, and temperature characteristics are X7R or X5R. Higher capacitance values help to improve load/line transient response. The output capacitance may be increased to keep low undershoot/overshoot. Place output capacitor as close as possible to VOUT and GND pins.

■ Dropout Voltage

The dropout voltage refers to the voltage difference between the VIN and VOUT pins while operating at specific output current. The dropout voltage V_{DROP} also can be expressed as the voltage drop on the pass-FET at specific output current (I_{RATED}) while the pass-FET is fully operating at ohmic region and the pass-FET can be characterized as a resistance $R_{\text{DS(ON)}}$. Thus the dropout voltage can be defined as ($V_{\text{DROP}} = V_{\text{IN}} - V_{\text{OUT}} = R_{\text{DS(ON)}} \times I_{\text{RATED}}$). For normal operation, the suggested LDO operating range is ($V_{\text{IN}} > V_{\text{OUT}} + V_{\text{DROP}}$) for good transient response and PSRR ability. Vice versa, while operating at the ohmic region will degrade the performance severely.

■ Thermal Application

For continuous operation, do not exceed the absolute maximum junction temperature. The maximum power dissipation depends on the thermal resistance of the IC package, PCB layout, rate of surrounding airflow, and difference between junction and ambient temperature. The maximum power dissipation can be calculated as below:

$T_A = 25^\circ\text{C}$, AISIS DEMO PCB

The max $P_D = (T_j - T_A) / \theta_{JA}$.

Power dissipation (P_D) is equal to the product of the output current and the voltage drop across the output pass element, as shown in the equation below:

$$P_D = (V_{IN} - V_{OUT}) \times I_{OUT}$$

■ Layout Consideration

By placing input and output capacitors on the same side of the PCB as the LDO, and placing them as close as is practical to the package can achieve the best performance. The ground connections for input and output capacitors must be back to the HM73XXH ground pin using as wide and as short of a copper trace as is practical. Connections using long trace lengths, narrow trace widths, and/or connections through via must be avoided. These add parasitic inductances and resistance that results in worse performance especially during transient conditions.